

Triac Low Power Use

REJ03G0292-0200					
Rev.2.00					
Mar 22, 2007					

# Features

- I<sub>T (RMS)</sub> : 0.8 A
- V<sub>DRM</sub>: 600 V
- $I_{FGTI}$ ,  $I_{RGTI}$ ,  $I_{RGT}$  : 5 mA
- I<sub>FGT</sub> : 10 mA

- Non-Insulated Type
- Planar Passivation Type
- Completed Pb Free

# Outline



# Applications

Hybrid IC, solid state relay, electric fan, washing machine, and other general purpose control applications

# **Maximum Ratings**

Parameter	Symbol	Voltage class	Unit	
raiameter	Symbol	12 (Mark BF)		
Repetitive peak off-state voltage <sup>Note1</sup>	V <sub>DRM</sub>	600	V	
Non-repetitive peak off-state voltage <sup>Note1</sup>	V <sub>DSM</sub>	720	V	

Parameter	Symbol	Ratings	Unit	Conditions
RMS on-state current	I <sub>T (RMS)</sub>	0.8	A	Commercial frequency, sine full wave $360^{\circ}$ conduction, Ta = $40^{\circ}C^{Note3}$
Surge on-state current	I <sub>TSM</sub>	8	A	60Hz sinewave 1 full cycle, peak value, non-repetitive
I <sup>2</sup> t for fusing	l <sup>2</sup> t	0.26	A <sup>2</sup> s	Value corresponding to 1 cycle of half wave 60Hz, surge on-state current
Peak gate power dissipation	P <sub>GM</sub>	1	W	
Average gate power dissipation	P <sub>G (AV)</sub>	0.1	W	
Peak gate voltage	V <sub>GM</sub>	10	V	
Peak gate current	I <sub>GM</sub>	1	A	
Junction temperature	Tj	- 40 to +125	°C	
Storage temperature	Tstg	- 40 to +125	°C	
Mass	—	50	mg	Typical value

Notes: 1. Gate open.

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# **Electrical Characteristics**

Parameter		Symbol	Min.	Тур.	Max.	Unit	Test conditions
Repetitive peak off-state current		I <sub>DRM</sub>	—	—	2.0	mA	Tj = 125°C, V <sub>DRM</sub> applied
On-state voltage		V <sub>TM</sub>	—	—	2.0	V	Tc = $25^{\circ}$ C, I <sub>TM</sub> = 1.2 A, Instantaneous measurement
Gate trigger voltage <sup>Note2</sup>	Ι	V <sub>FGTI</sub>	_	_	2.0	V	$Tj = 25^{\circ}C, V_D = 6 V, R_L = 6 \Omega,$
	II	V <sub>RGTI</sub>	—	—	2.0	V	$R_G = 330 \Omega$
	III	V <sub>RGTIII</sub>	—	—	2.0	V	
	IV	V <sub>FGTIII</sub>	—	—	2.0	V	
Gate trigger current <sup>Note2</sup>	Ι	I <sub>FGTI</sub>	—	—	5	mA	$\label{eq:Tj} \begin{array}{l} Tj=25^\circC,V_D=6\;V,R_L=6\;\Omega,\\ R_G=330\;\Omega \end{array}$
	II	I <sub>RGTI</sub>	_	_	5	mA	
	III	I <sub>RGTIII</sub>	_	_	5	mA	
	IV	I <sub>FGTIII</sub>	—	—	10	mA	
Gate non-trigger voltage		$V_{GD}$	0.1	—	—	V	$Tj = 125^{\circ}C, V_D = 1/2 V_{DRM}$
Thermal resistance		R <sub>th (j-a)</sub>	_	_	65	°C/W	Junction to ambient <sup>Note3</sup>
Critical-rate of rise of off-state commutating voltage <sup>Note4</sup>		(dv/dt)c	0.5	_	_	V/µs	Tj = 125°C

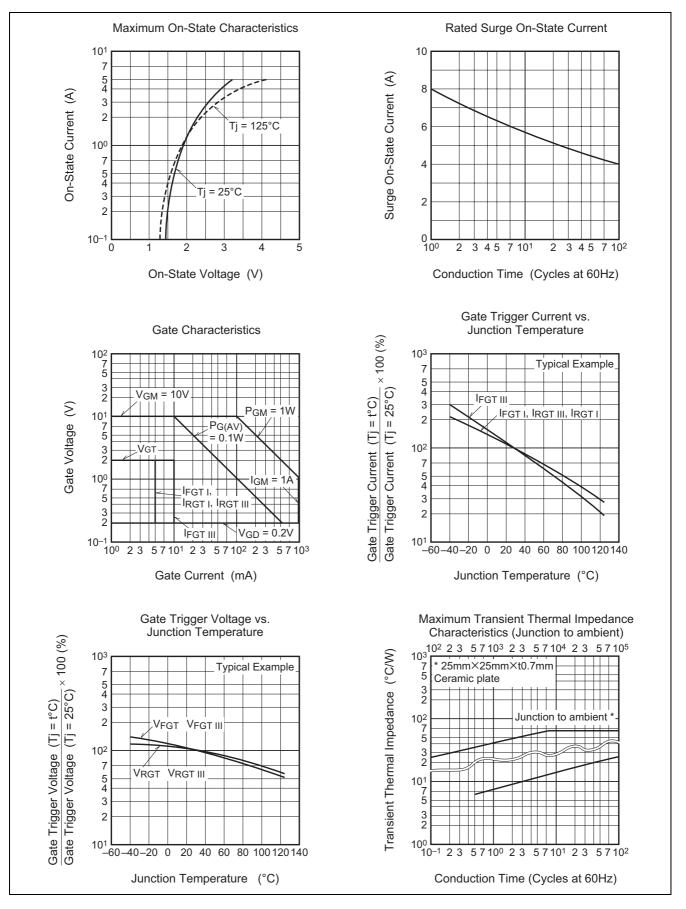
Notes: 2. Measurement using the gate trigger characteristics measurement circuit.

3. Soldering with ceramic plate (25 mm  $\times$  25 mm  $\times$  t0.7 mm).

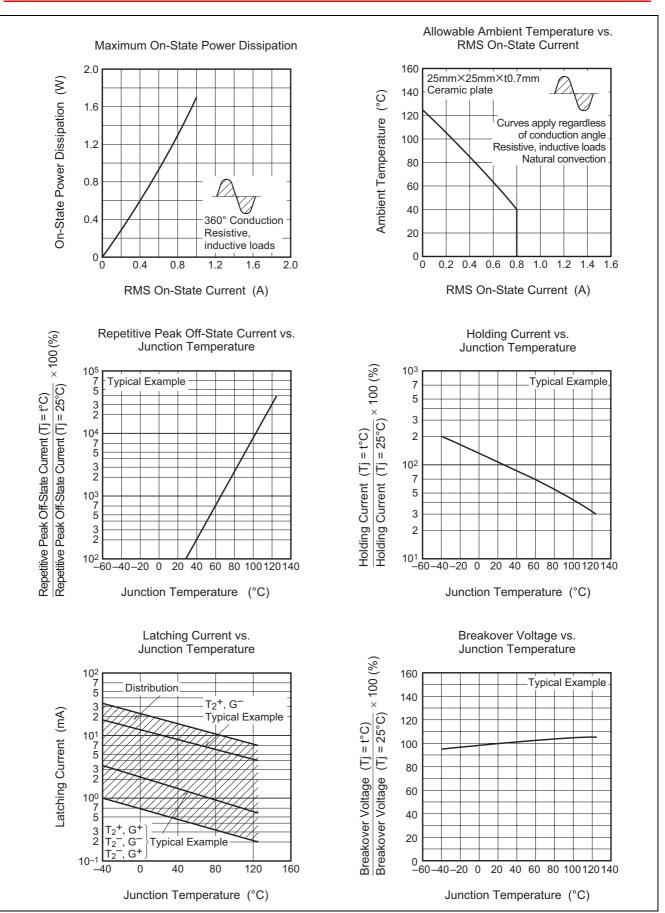
4. Test conditions of the critical-rate of rise of off-state commutating voltage is shown in the table below.

Test conditions	Commutating voltage and current waveforms (inductive load)		
1. Junction temperature Tj = 125°C	Supply Voltage → Time		
2. Rate of decay of on-state commutating current (di/dt)c = - 0.4 A/ms	Main Current → Time		
3. Peak off-state voltage V <sub>D</sub> = 400 V	Main VoltageTime (dv/dt)c VD		

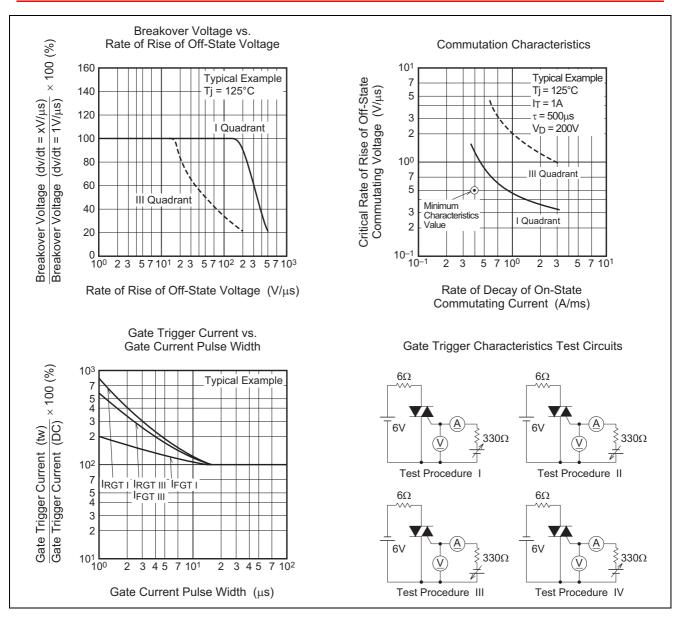
## **Performance Curves**



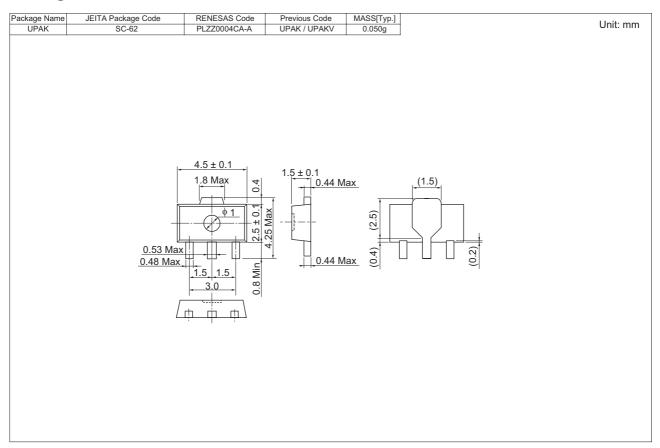
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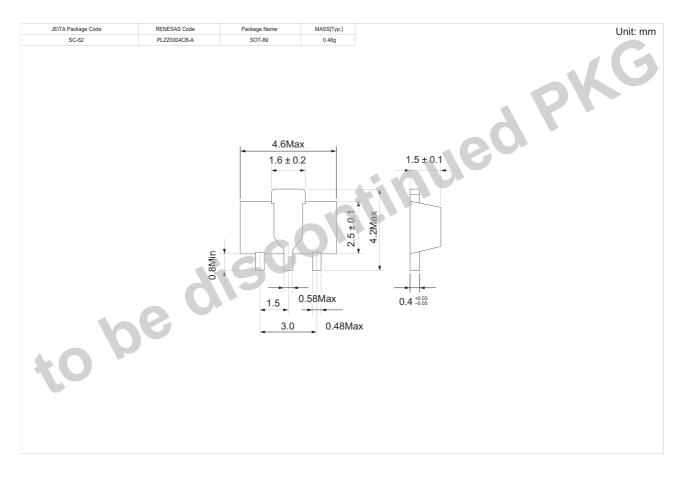


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# **Package Dimensions**





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# **Order Code**

Lead form	Standard packing	Quantity	Standard order code	Standard order code example
Surface-mounted type	Taping	4000	Type name +A –T +Direction (1 or 2)+4	BCR08AS-12A-T14

Note : Please confirm the specification about the shipping in detail.

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